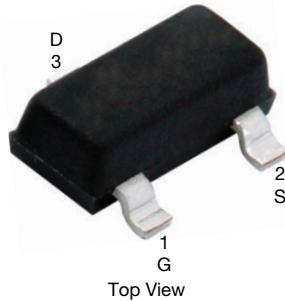


Automotive P-Channel 40 V (D-S) 175 °C MOSFET

SOT-23 (TO-236)



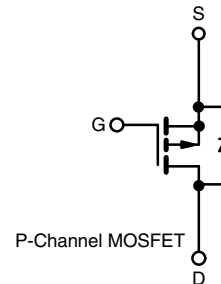
Marking Code: 9Axxx

PRODUCT SUMMARY	
V_{DS} (V)	-40
$R_{DS(on)}$ (Ω) at $V_{GS} = -10$ V	0.094
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	0.188
I_D (A)	-4.1
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE


RoHS
 COMPLIANT
 HALOGEN
FREE


ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	SQ2389ES (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	-40	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	I_D	$T_C = 25$ °C	-4.1
		$T_C = 125$ °C	-2.4
Continuous source current (diode conduction)	I_S	-3.6	A
Pulsed drain current ^a	I_{DM}	-16	mJ
Single pulse avalanche current	I_{AS}	-12	
Single pulse avalanche energy	E_{AS}	7.2	
Maximum power dissipation ^a	P_D	$T_C = 25$ °C	3
		$T_C = 125$ °C	1
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R_{thJA}	166	°C/W
Junction-to-foot (drain)	R_{thJF}	50	

Notes

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)



SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-40	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1.5	-2.0	-2.5	
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = -40\text{ V}$	-	-	-1	μA
		$V_{GS} = 0\text{ V}, V_{DS} = -40\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	-50	
		$V_{GS} = 0\text{ V}, V_{DS} = -40\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	-150	
On-state drain current ^a	$I_{D(on)}$	$V_{GS} = -10\text{ V}, V_{DS} \leq -5\text{ V}$	-10	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -3\text{ A}$	-	0.084	0.094	Ω
		$V_{GS} = -10\text{ V}, I_D = -3\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.144	
		$V_{GS} = -10\text{ V}, I_D = -3\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.169	
		$V_{GS} = -4.5\text{ V}, I_D = -3\text{ A}$	-	0.140	0.188	
Forward transconductance ^b	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -3\text{ A}$	-	5	-	S
Dynamic ^b						
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -20\text{ V}, f = 1\text{ MHz}$	-	360	420	μF
Output capacitance	C_{oss}		-	80	100	
Reverse transfer capacitance	C_{rss}		-	42	54	
Total gate charge ^c	Q_g	$V_{GS} = -10\text{ V}, V_{DS} = -20\text{ V}, I_D = -3\text{ A}$	-	8.2	12	nC
Gate-source charge ^c	Q_{gs}		-	1.1	-	
Gate-drain charge ^c	Q_{gd}		-	3	-	
Gate resistance	R_g	$f = 1\text{ MHz}$	3.1	4.1	7	Ω
Turn-on delay time ^c	$t_{d(on)}$	$V_{DD} = -20\text{ V}, R_L = 6.7\text{ }\Omega, I_D \cong -3\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$	-	7	10	ns
Rise time ^c	t_r		-	12	16	
Turn-off delay time ^c	$t_{d(off)}$		-	16	20	
Fall time ^c	t_f		-	4	8	
Source-Drain Diode Ratings and Characteristics ^b						
Pulsed current ^a	I_{SM}		-	-	-10	A
Forward voltage	V_{SD}	$I_F = -1.5\text{ A}, V_{GS} = 0\text{ V}$	-	-0.8	-1.2	V

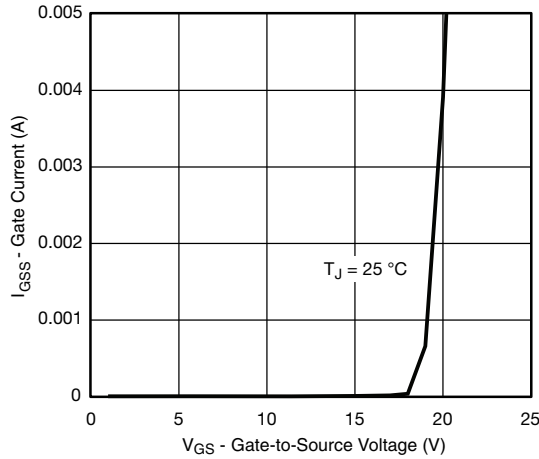
Notes

- c. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\text{ }\%$
- d. Guaranteed by design, not subject to production testing
- e. Independent of operating temperature

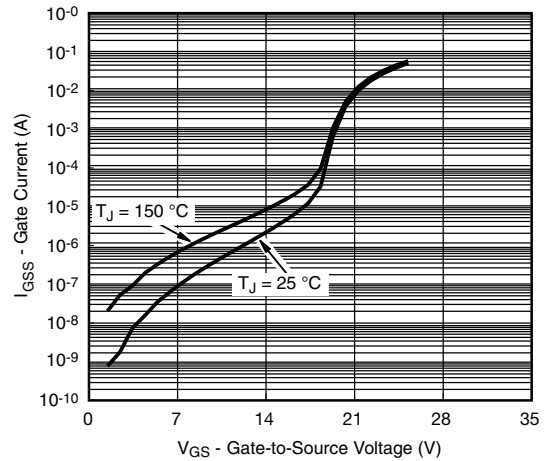
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



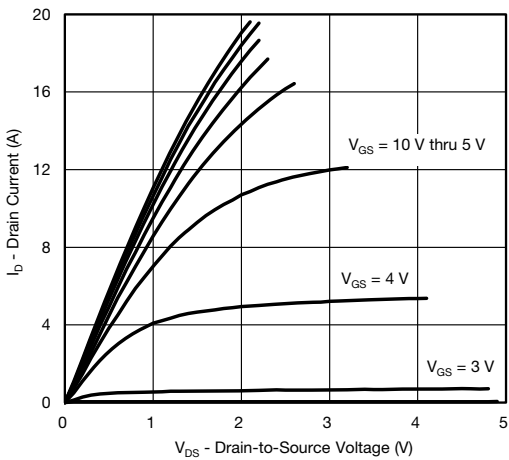
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



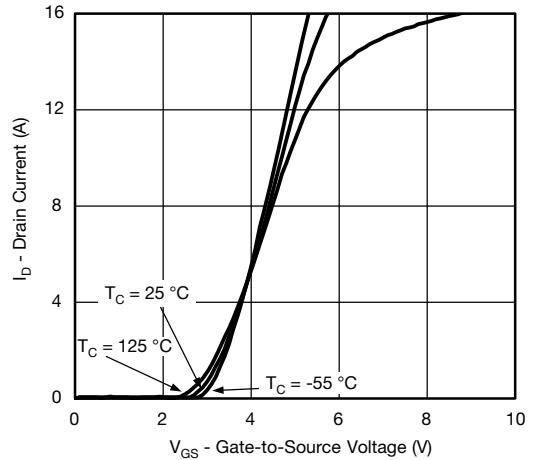
Gate Current vs. Gate-Source Voltage



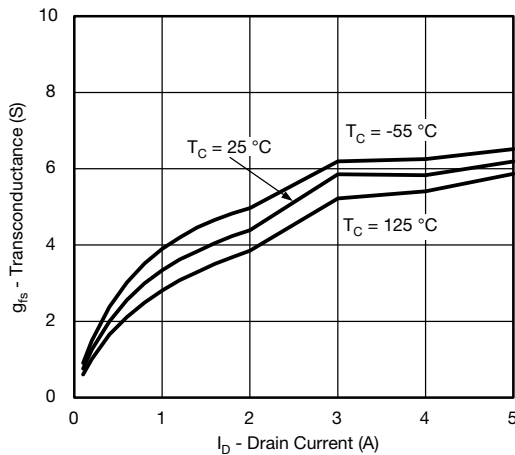
Gate Current vs. Gate-Source Voltage



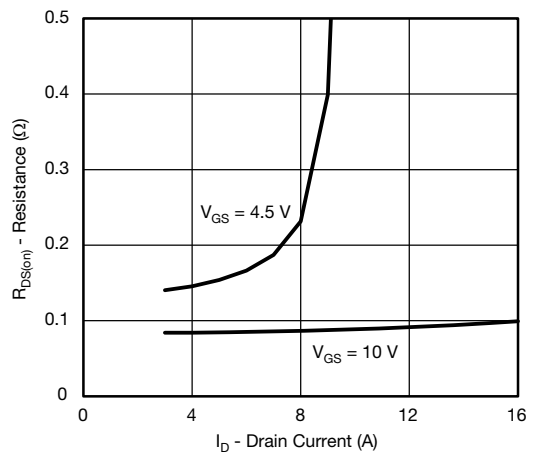
Output Characteristics



Transfer Characteristics



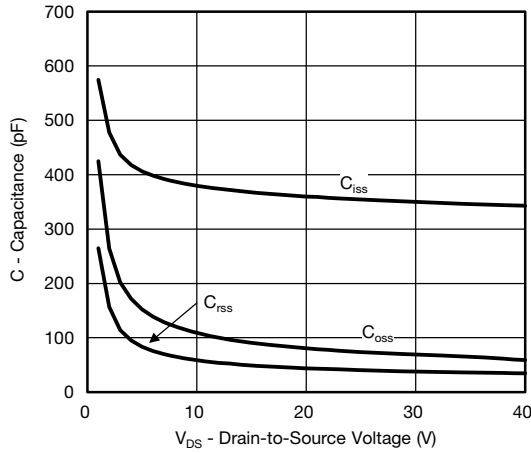
Transconductance



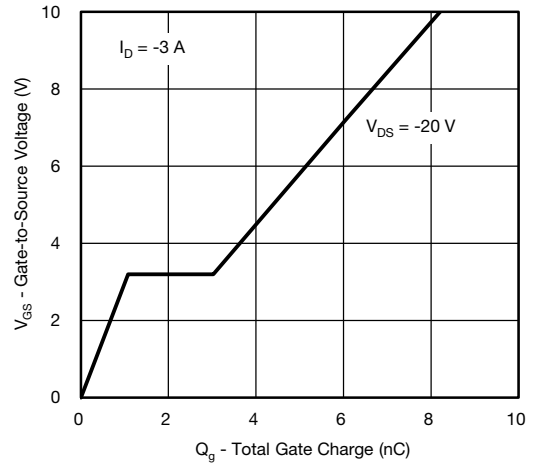
On-Resistance vs. Drain Current



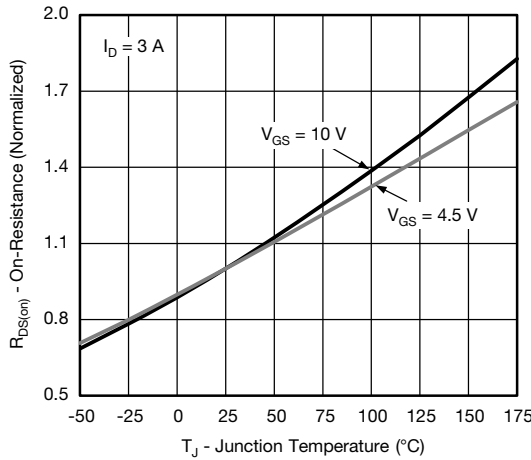
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



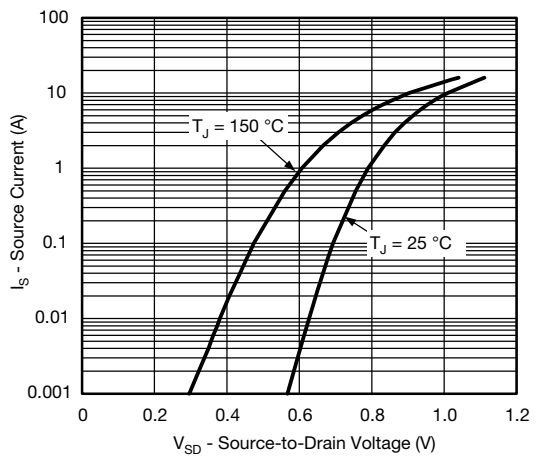
Capacitance



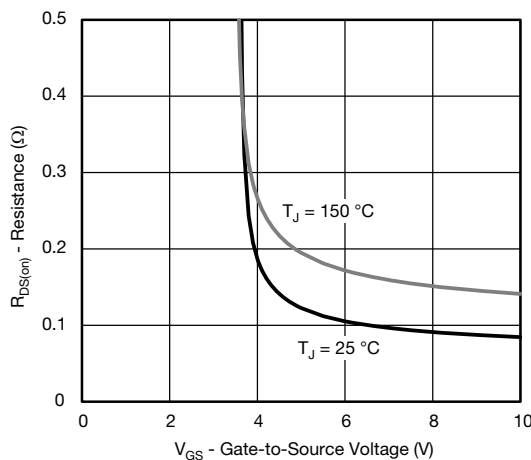
Gate Charge



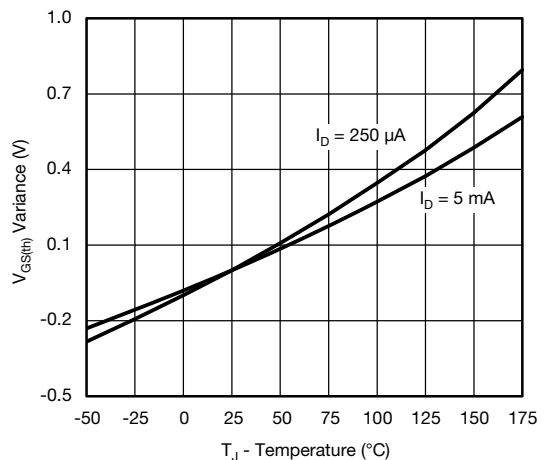
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



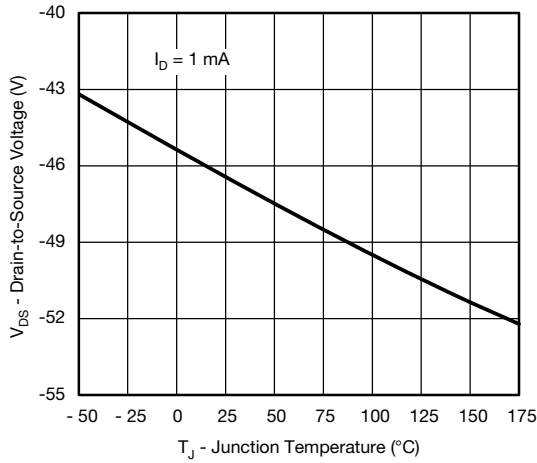
On-Resistance vs. Gate-Source Voltage



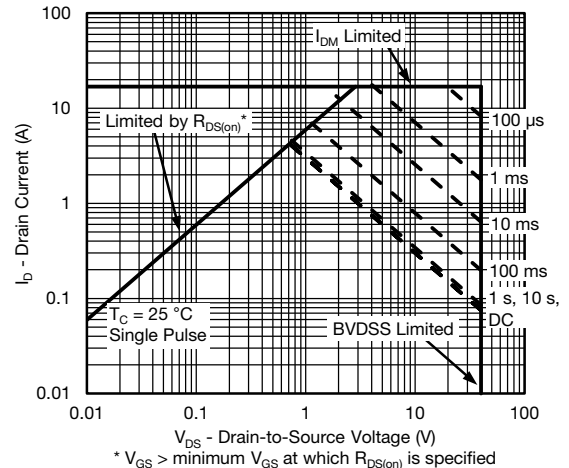
Threshold Voltage



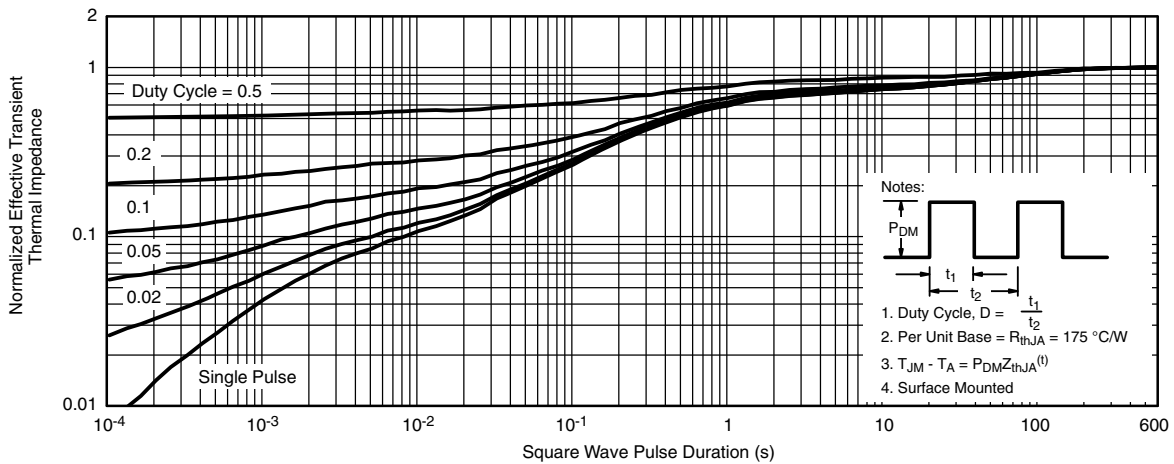
THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Drain Source Breakdown vs. Junction Temperature



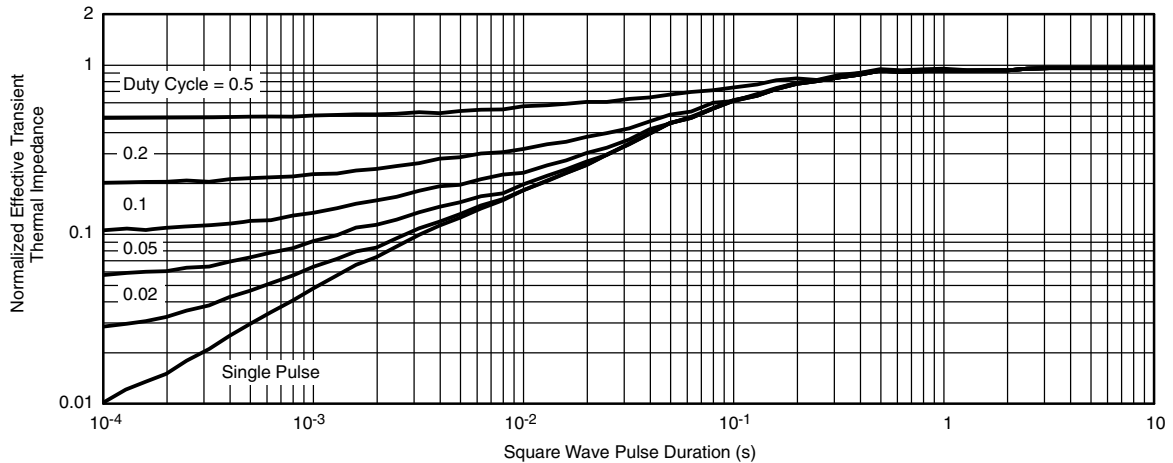
Safe Operating Area
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

ECN: S-03946-Rev. K, 09-Jul-01
 DWG: 5479

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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